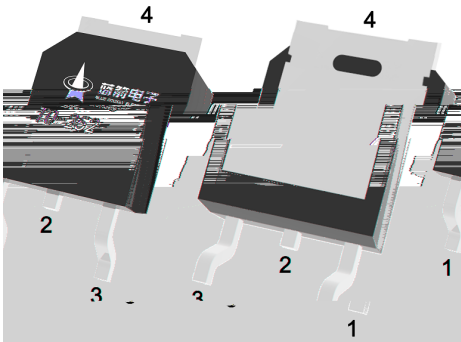
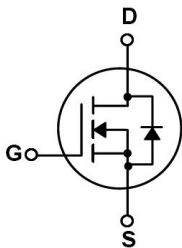


SiC

$\leq$	Ω	Ω
$\leq$	Ω	Ω

LED	PD	PC
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		Ω μ				
-						μ
-						
						Ω

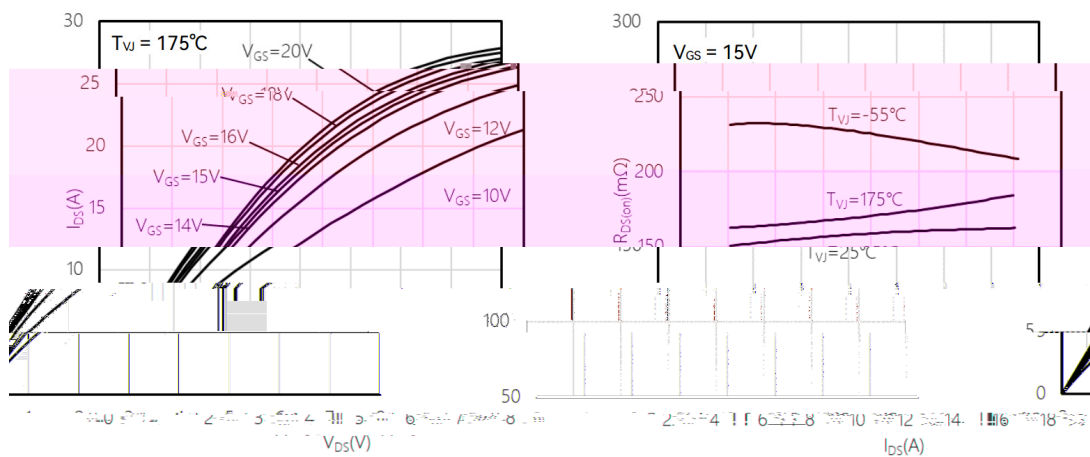
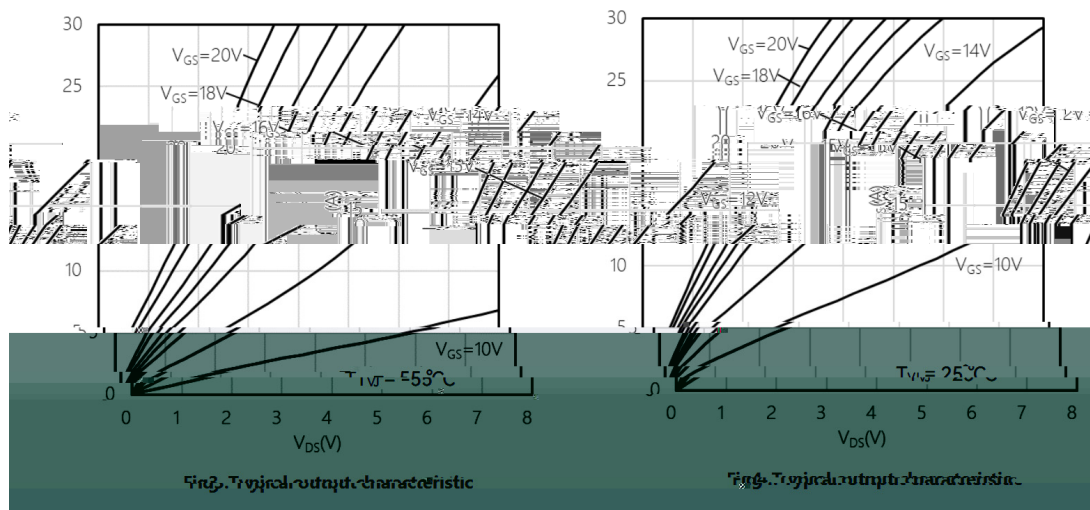
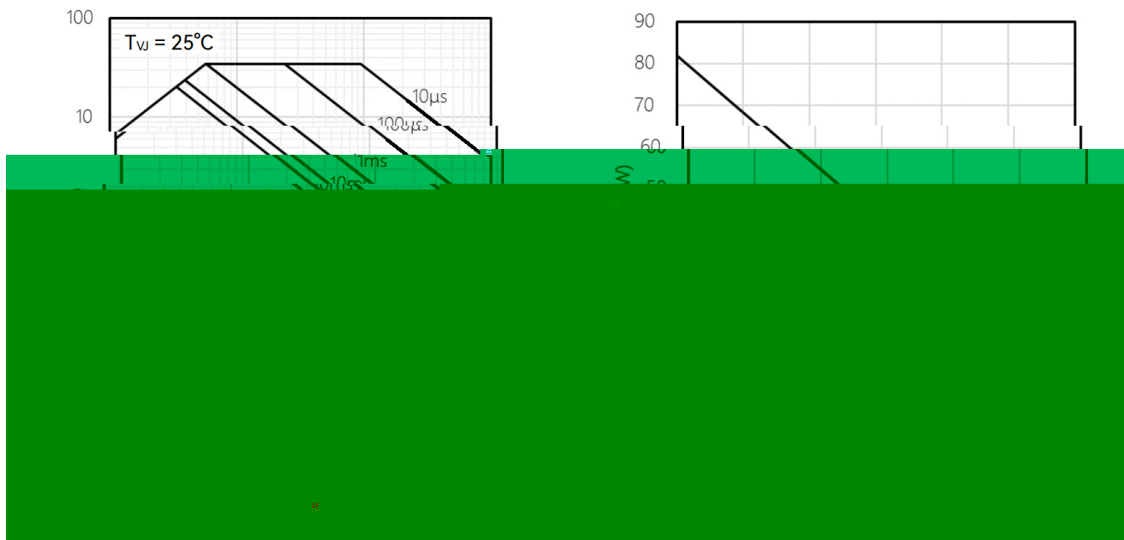
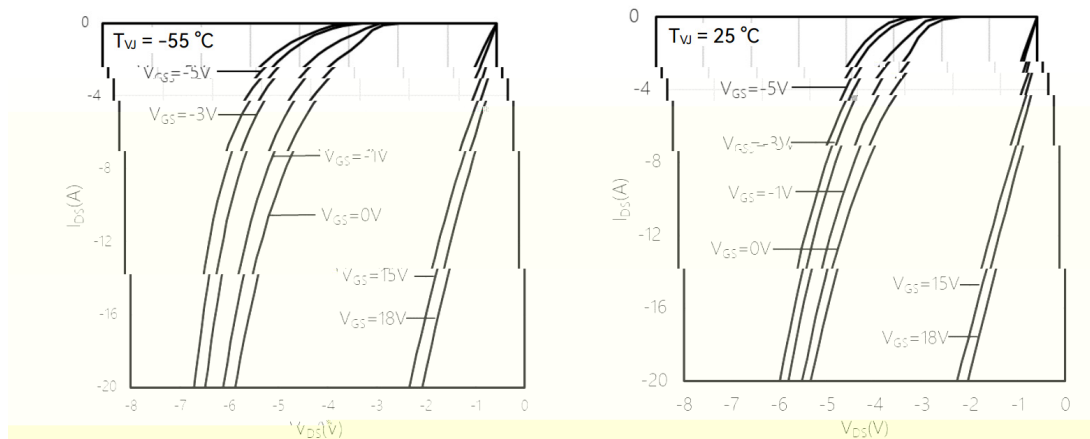
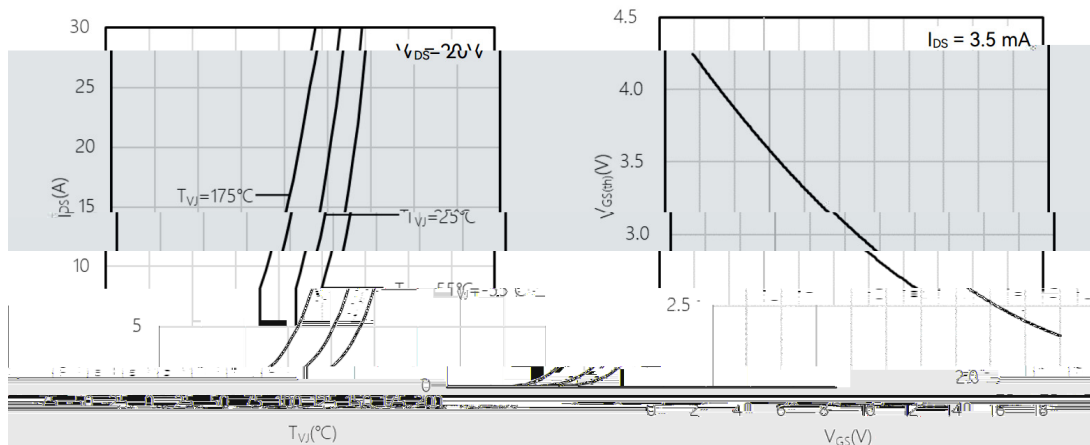
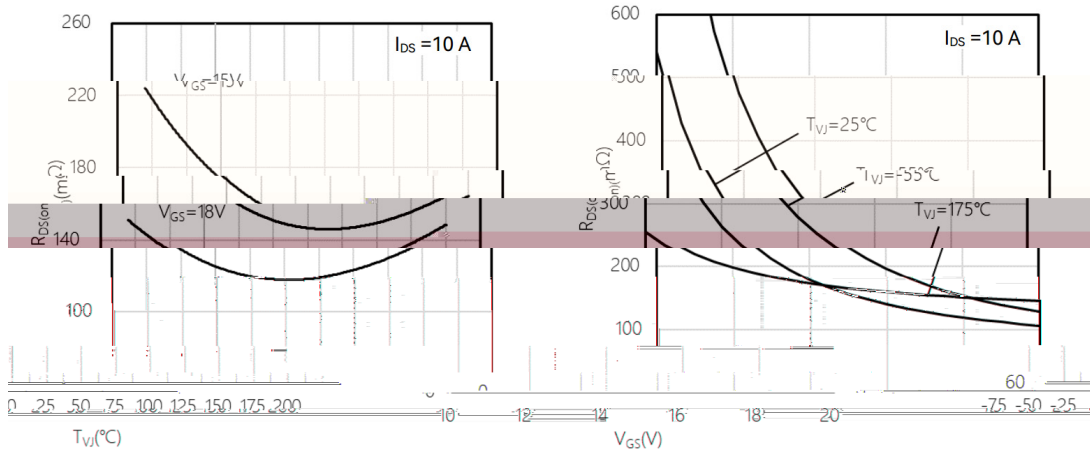


Fig5. Typical output characteristic

Fig6. Typical on-state resistance as a function of drain current



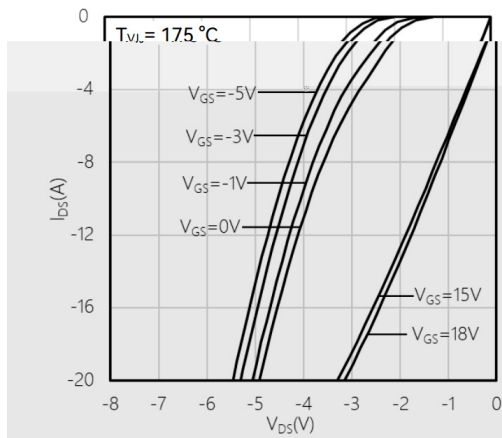


Fig13. Typical reverse drain current as function of reverse drain voltage

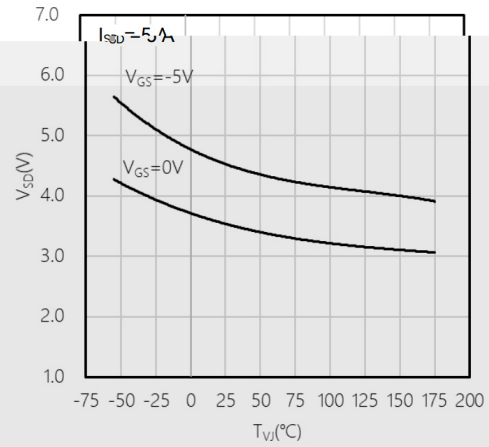


Fig14. Typical reverse drain voltage as function of junction temperature

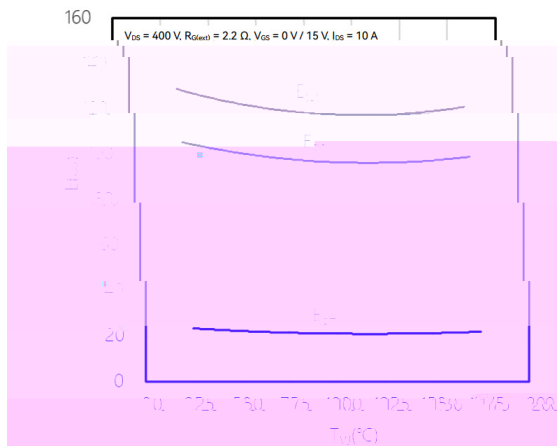


Fig15. Typical switching energy as a function of junction temperature

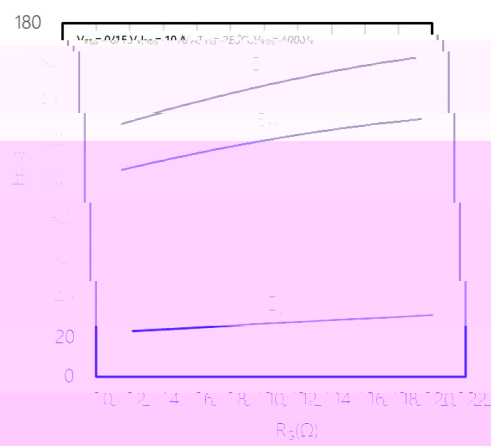


Fig16. Typical switching energy as a function of drain resistance

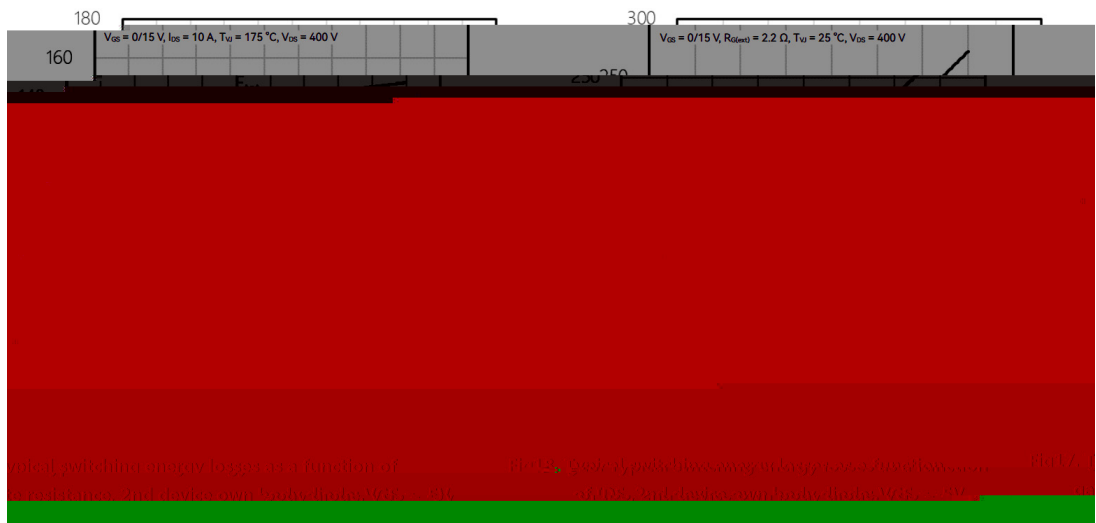


Fig17. Typical switching energy as a function of gate resistance

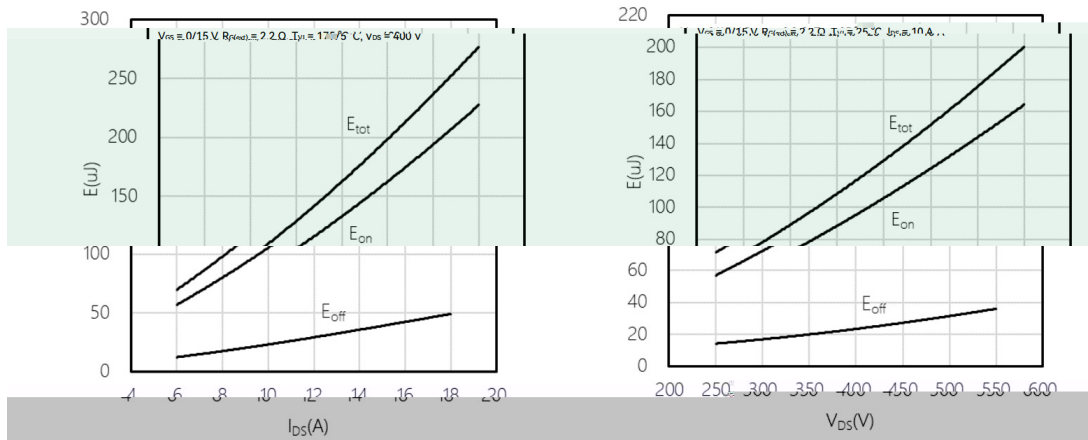


Fig. 20: Typical switching energy losses as a function

Fig. 21: Typical switching energy losses as a function

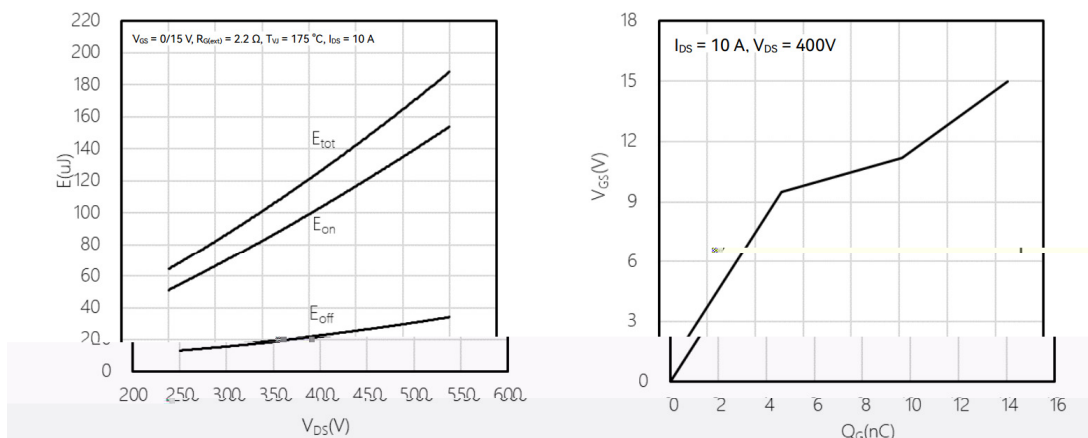


Fig. 22: Typical switching energy losses as a function of V_{DS} , 2nd device own body diode: $V_{GS} = -5V$

Fig. 23: typical gate charge

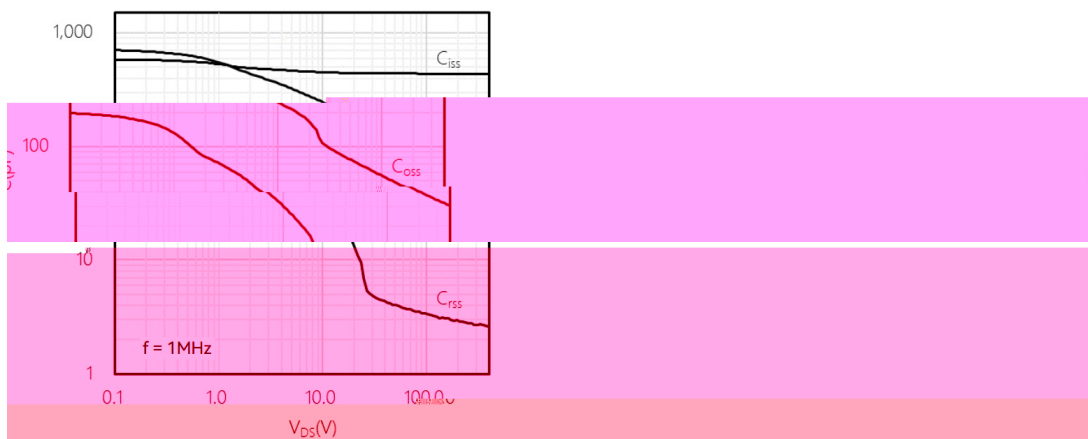


Fig. 24: Typical capacitance as a function of drain-source voltage

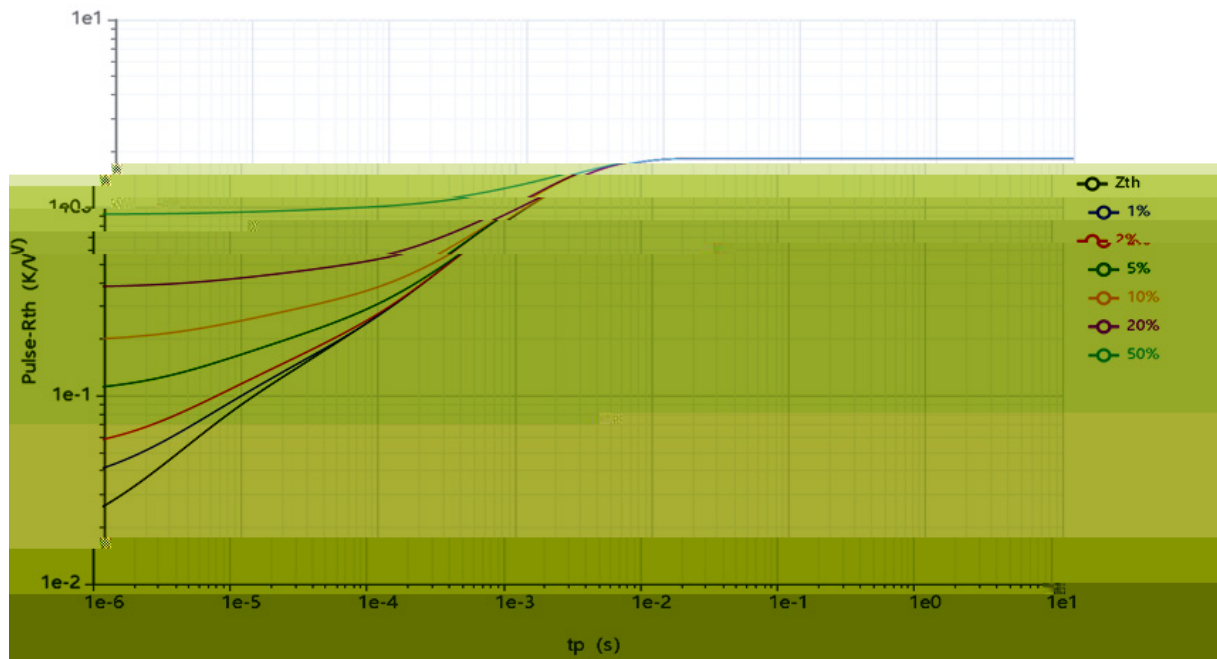
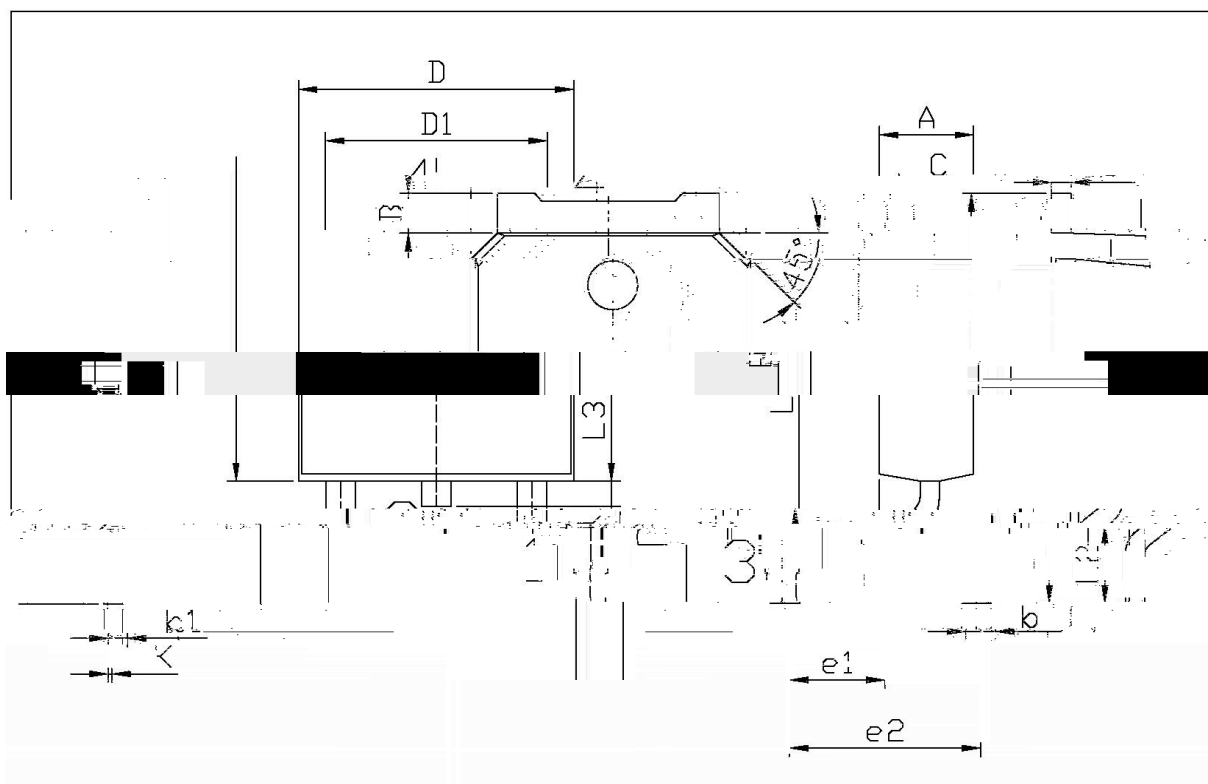
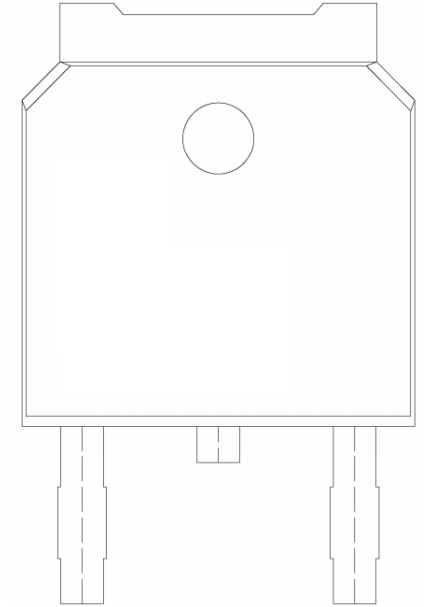


Fig24. Transient thermal resistance (MOSFET)



单位: mm

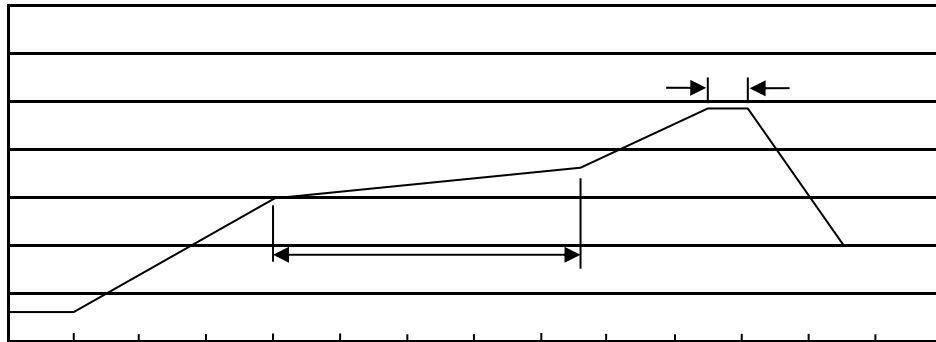
Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
5.95	6.25		A	2.20	2.40
2.24	2.34		"B	0.95	1.25
4.42	4.73		b	0.70	0.90
9.85	10.35		b1	0.45	0.55
0.60	0.90		L2	6.45	6.75
0.60	0.90	0.10	D1	5.10	5.50



65R180Z

SC

Temperature Profile for IR Reflow Soldering(Pb-Free)



±

±

±

±

±

±

	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box

	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box